

3Ω Single SPST Analog Switches

ABSOLUTE MAXIMUM RATINGS

V+ to GND-0.3V to +6V
 V- to GND+0.3V to -6V
 V+ to V-12V
 IN to GND-0.3V to (V+ + 0.3V)
 All Other Pins (Note 1)(V- - 0.3V) to (V+ + 0.3V)
 Continuous Current (NO, NC, COM)±100mA
 Peak Current (NO, NC, COM, pulsed at 1ms
 (10% duty cycle).....±200mA

Continuous Power Dissipation (T_A = +70°C)
 6-Pin SOT23 (derate 8.7mW/°C above +70°C).....691mW
 Operating Temperature Range-40°C to +85°C
 Junction Temperature+150°C
 Storage Temperature Range-65°C to +150°C
 Lead Temperature (soldering, 10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note 1: Signals on NO, NC, COM, or IN exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current rating.

ELECTRICAL CHARACTERISTICS—DUAL SUPPLIES

(V+ = +5V ±10%, V- = -5V ±10%, GND = 0, V_{IH} = +2.4V, V_{IL} = 0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Input Voltage Range	V _{COM} , V _{NO} , V _{NC}			V-		V+	V
On-Resistance	R _{ON}	V+ = 4.5V, V- = -4.5V, I _{COM} = 50mA; V _{NO} or V _{NC} = ±3.3V	T _A = +25°C	2.4	3	Ω	
			T _A = T _{MIN} to T _{MAX}	4			
On-Resistance Flatness (Note 4)	R _{FLAT}	V+ = 4.5V, V- = -4.5V, I _{COM} = 50mA; V _{NO} or V _{NC} = ±3.3V, 0	T _A = +25°C	0.4	0.7	Ω	
			T _A = T _{MIN} to T _{MAX}	1.0			
NC or NO Off-Leakage Current	I _{N(OFF)}	V+ = 5.5V, V- = -5.5V, V _{COM} = 4.5V; V _{NO} or V _{NC} = ±4.5V	T _A = +25°C	-1	0.1	1	nA
			T _A = T _{MIN} to T _{MAX}	-10	10		
COM Off-Leakage Current	I _{COM(OFF)}	V+ = 5.5V, V- = -5.5V, V _{COM} = +4.5V; V _{NO} or V _{NC} = ±4.5V	T _A = +25°C	-1	0.1	1	nA
			T _A = T _{MIN} to T _{MAX}	-10	10		
COM On-Leakage Current	I _{COM(ON)}	V+ = 5.5V, V- = -5.5V, V _{COM} = ±4.5V; V _{NO} or V _{NC} = ± 4.5V or floating	T _A = +25°C	-2	0.1	2	nA
			T _A = T _{MIN} to T _{MAX}	-20	20		
LOGIC INPUT							
Input Low Voltage	V _{IL}					0.8	V
Input High Voltage	V _{IH}			2.4			V
Input Leakage Current	I _{IN}			-1	0.005	1	μA
DYNAMIC							
Turn-On Time	t _{ON}	V+ = +4.5V, V- = -4.5V; V _{NO} or V _{NC} = 3.3V, R _L = 300Ω, C _L = 35pF, Figure 2	T _A = +25°C	135	300	ns	
			T _A = T _{MIN} to T _{MAX}	375			
Turn-Off Time	t _{OFF}	V+ = +4.5V, V- = -4.5V; V _{NO} or V _{NC} = 3.3V, R _L = 300Ω, C _L = 35pF, Figure 2	T _A = +25°C	50	110	ns	
			T _A = T _{MIN} to T _{MAX}	125			

3Ω Single SPST Analog Switches

ELECTRICAL CHARACTERISTICS—DUAL SUPPLIES (continued)

(V₊ = +5V ±10%, V₋ = -5V ±10%, GND = 0, V_{IH} = +2.4V, V_{IL} = 0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Charge Injection	Q	R _{GEN} = 0Ω, C _L = 1nF, V _{GEN} = 0, Figure 3	T _A = +25°C		87		pC
Off-Isolation	V _{ISO}	R _L = 50Ω, C _L = 5pF, f = 1MHz, Figure 4	T _A = +25°C		-75		dB
On-Channel Bandwidth (-3dB)	BW	R _S = 50Ω, R _L = 50Ω			250		MHz
NC or NO Off-Capacitance	C _(N_OFF)	f = 1MHz, Figure 5	T _A = +25°C		85		pF
COM Off-Capacitance	C _(COMOFF)	f = 1MHz, Figure 5	T _A = +25°C		85		pF
On-Capacitance	C _(ON)	f = 1MHz, Figure 5	T _A = +25°C		350		pF
POWER SUPPLY							
Supply Voltage	V ₊ , V ₋			±2.7		±5.5	V
Positive Supply Current	I ₊	V _{IN} = 0 or 5.5V, V ₊ = 5.5V, V ₋ = -5.5V	T _A = +25°C		0.002	1	μA
			T _A = T _{MIN} to T _{MAX}			10	
Negative Supply Current	I ₋	V _{IN} = 0 or 5.5V, V ₊ = 5.5V, V ₋ = -5.5V	T _A = +25°C	-1	-0.002		μA
			T _A = T _{MIN} to T _{MAX}	-10			

ELECTRICAL CHARACTERISTICS—SINGLE SUPPLY

(V₊ = +5V ±10%, V₋ = 0, GND = 0, V_{IH} = +2.4V, V_{IL} = 0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Input Voltage Range	V _{COM} , V _{NO} , V _{NC}			0		V+	V
On-Resistance	R _{ON}	V+ = 4.5V; I _{COM} = 50mA; V _{NO} or V _{NC} = 3.3V	T _A = +25°C	3.5	5.75	Ω	
			T _A = T _{MIN} to T _{MAX}	7.5			
On-Resistance Flatness (Note 4)	R _{FLAT}	V+ = 4.5V; I _{COM} = 50mA; V _{NO} or V _{NC} = 1.5V, 2.5V, 3.3V	T _A = +25°C	0.4	1.6	Ω	
			T _A = T _{MIN} to T _{MAX}	2			
NC or NO Off-Leakage Current	I _{N(OFF)}	V+ = 5.5V; V _{NO} or V _{NC} = 4.5V or 0; V _{COM} = 0 or 4.5V	T _A = +25°C	-1	0.1	1	nA
			T _A = T _{MIN} to T _{MAX}	-10		10	
COM Off-Leakage Current	I _{COM(OFF)}	V+ = 5.5V; V _{NO} or V _{NC} = 4.5V or 0; V _{COM} = 0 or 4.5V	T _A = +25°C	-1	0.1	1	nA
			T _A = T _{MIN} to T _{MAX}	-10		10	

3Ω Single SPST Analog Switches

ELECTRICAL CHARACTERISTICS—SINGLE SUPPLY (continued)

(V+ = +5V ±10%, V- = 0, GND = 0, V_{IH} = +2.4V, V_{IL} = 0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
COM On-Leakage Current	I _{COM (ON)}	V ₊ = 5.5V; V _{NO} or V _{NC} = 0, 4.5V, or floating; V _{COM} = 0 or 4.5V	T _A = +25°C	-2	0.2	2	nA
			T _A = T _{MIN} to T _{MAX}	-20		20	
LOGIC INPUT							
Input Low Voltage	V _{IL}			0.8			V
Input High Voltage	V _{IH}			2.4			V
Input Leakage Current	I _{IN}			-1	0.005	1	μA
DYNAMIC							
Turn-On Time	t _{ON}	V ₊ = +4.5V; V _{NO} or V _{NC} = +3.3V, R _L = 300Ω, C _L = 35pF, Figure 2	T _A = +25°C	350	700	ns	
			T _A = T _{MIN} to T _{MAX}		850		
Turn-Off Time	t _{OFF}	V ₊ = +4.5V; V _{NO} or V _{NC} = +3.3V, R _L = 300Ω, C _L = 35pF, Figure 2	T _A = +25°C	55	150	ns	
			T _A = T _{MIN} to T _{MAX}		160		
Charge Injection	Q	R _{GEN} = 0Ω, C _L = 1nF, V _{GEN} = 2.5V, Figure 3	T _A = +25°C	31		pC	
Off-Isolation	V _{ISO}	R _L = 50Ω, C _L = 5pF, f = 1MHz, Figure 4	T _A = +25°C	-65		dB	
On-Channel Bandwidth (-3dB)		R _S = 50Ω, R _L = 50Ω		150		MHz	
NC or NO Off-Capacitance	C _(N_OFF)	f = 1MHz, Figure 5	T _A = +25°C	85		pF	
COM Off-Capacitance	C _(COMOFF)	f = 1MHz, Figure 5	T _A = +25°C	85		pF	
On-Capacitance	C _(ON)	f = 1MHz, Figure 5	T _A = +25°C	350		pF	
POWER SUPPLY							
Supply Voltage	V ₊			2.7	5.5		V
Positive Supply Current	I ₊	V _{IN} = 0 or 5V, V ₊ = 5.5V	T _A = +25°C	0.002		1	μA
			T _A = T _{MIN} to T _{MAX}	10			

Note 2: Parameters are 100% tested at +25°C only and guaranteed by correlation through the full-rated temperature range.

Note 3: The algebraic convention, where the most negative value is a minimum and the most positive value a maximum, is used in this data sheet.

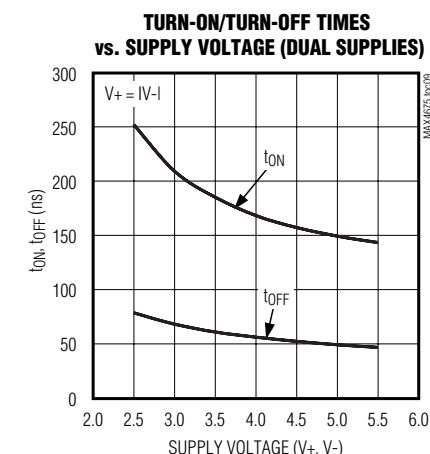
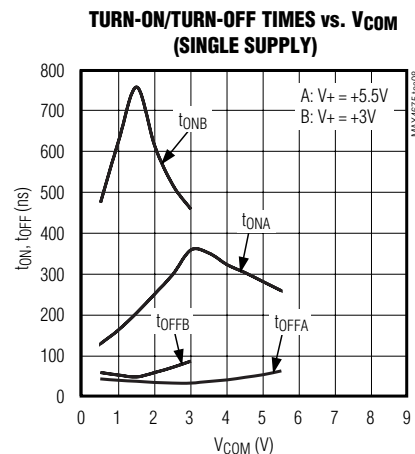
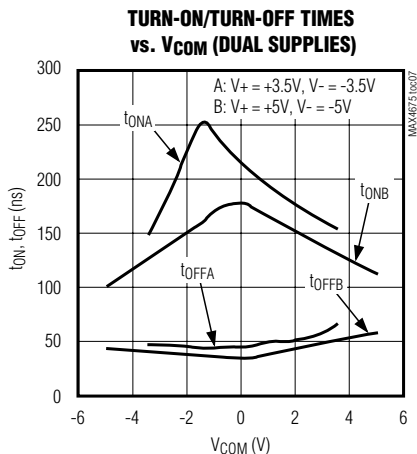
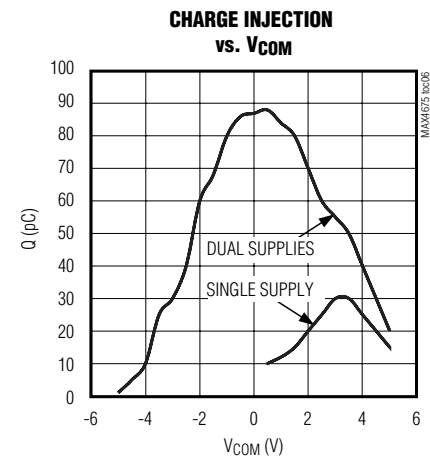
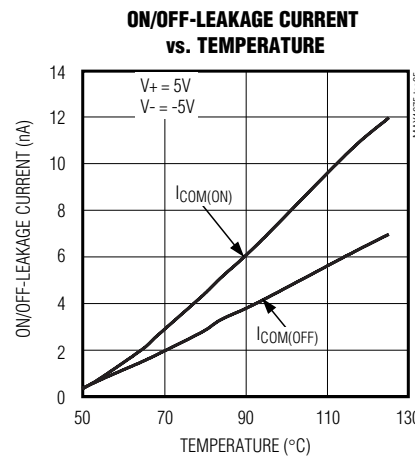
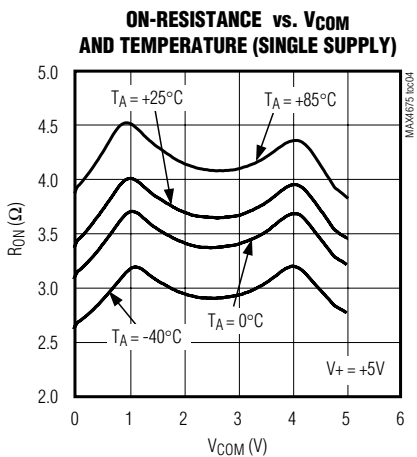
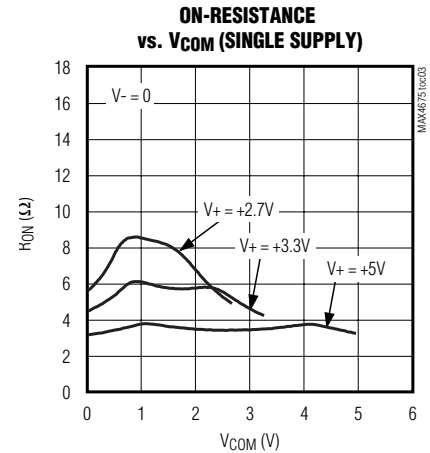
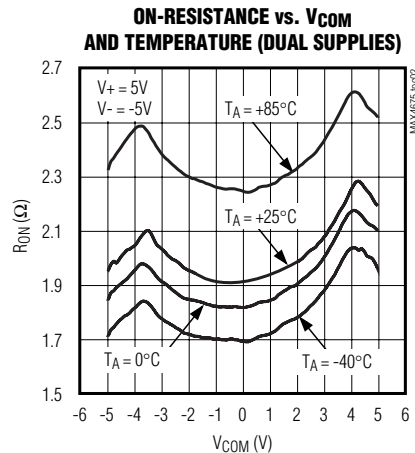
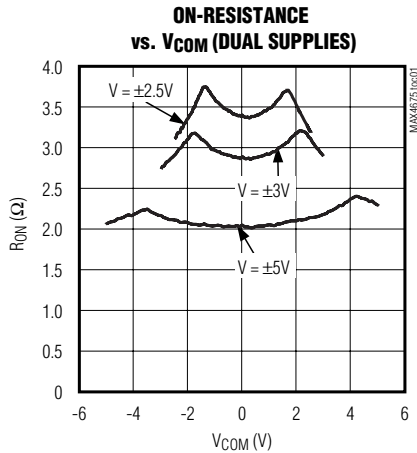
Note 4: Flatness is defined as the difference between the maximum and minimum value of R_{ON} as measured over the specified analog signal ranges.

3Ω Single SPST Analog Switches

Typical Operating Characteristics

($T_A = +25^\circ\text{C}$, unless otherwise noted.)

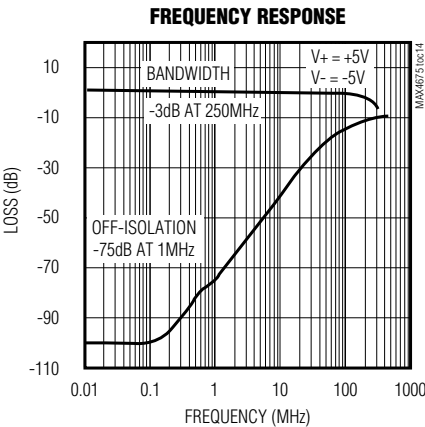
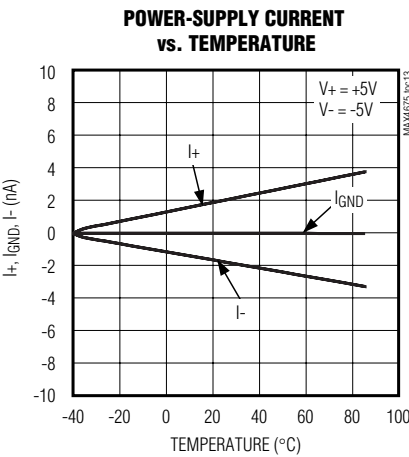
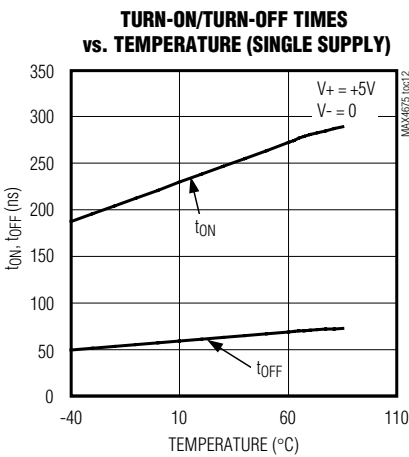
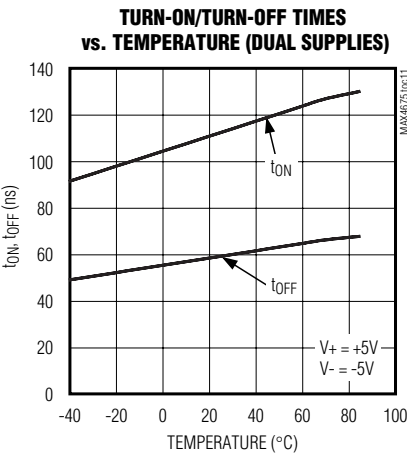
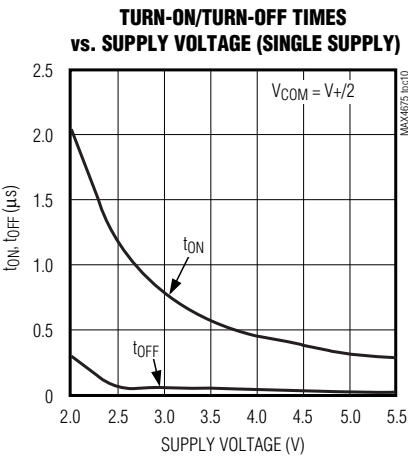
MAX4675/MAX4676



3Ω Single SPST Analog Switches

Typical Operating Characteristics (continued)

(T_A = +25°C, unless otherwise noted.)



Pin Description

PIN		NAME	FUNCTION
MAX4675	MAX4676		
1	1	V+	Positive Supply
2	2	COM	Analog Switch Common Terminals
3	3	V-	Negative Supply
4	4	GND	Ground
5	—	NO	Analog Switch Normally Open Terminal
—	5	NC	Analog Switch Normally Closed Terminal
6	6	IN	Logic Input

3Ω Single SPST Analog Switches

Applications Information

Overvoltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings can cause permanent damage to the devices. Always sequence V+ on first, then V-, followed by the logic inputs, NO, NC, or COM. If proper power-supply sequencing is not possible, add two small-signal diodes (D1, D2) in series with the supply pins (Figure 1). Adding diodes reduces the analog signal range to one diode drop below V+ and one diode drop above V- but does not affect the devices' low switch resistance and low leakage characteristics. Device operation is unchanged, and the difference between V+ and V- should not exceed 12V.

Power-supply bypassing improves noise margin and prevents switching noise from propagating from the V+ supply to other components. A 0.1μF capacitor connected from V+ to GND is adequate for most applications.

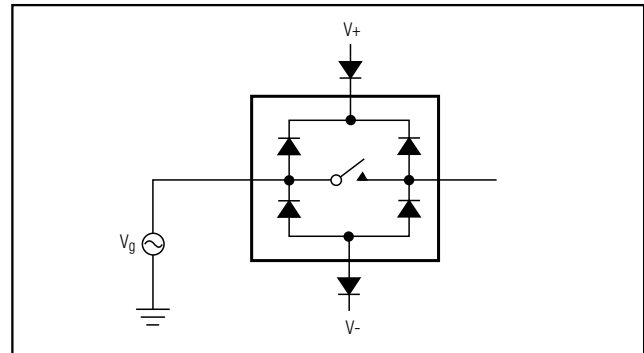


Figure 1. Overvoltage Protection Using External Blocking Diodes

Timing Diagrams/Test Circuits

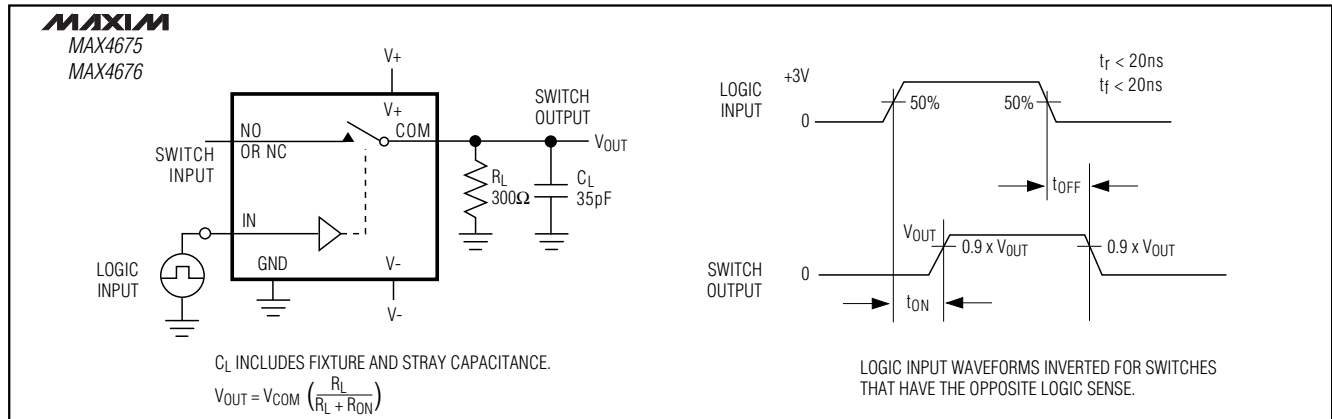


Figure 2. Switching Time

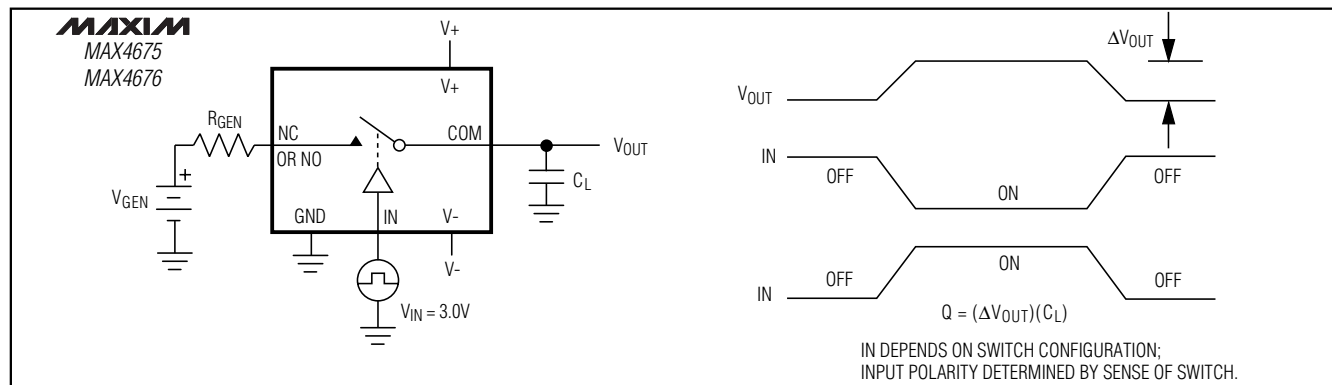


Figure 3. Charge Injection

3Ω Single SPST Analog Switches

Timing Diagrams/Test Circuits (continued)

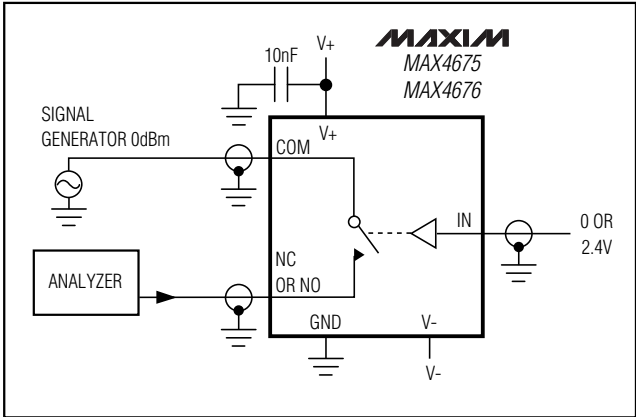


Figure 4. Off-Isolation/On-Channel Bandwidth

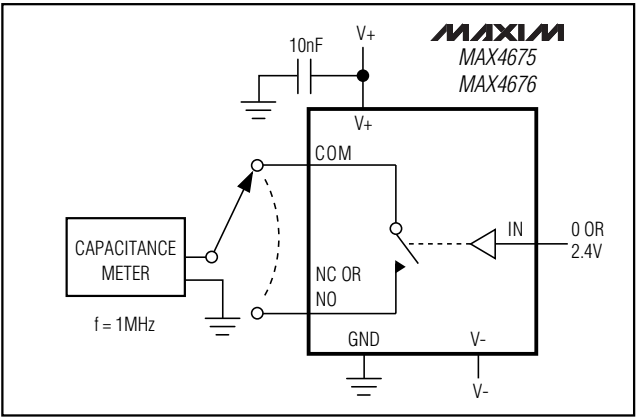
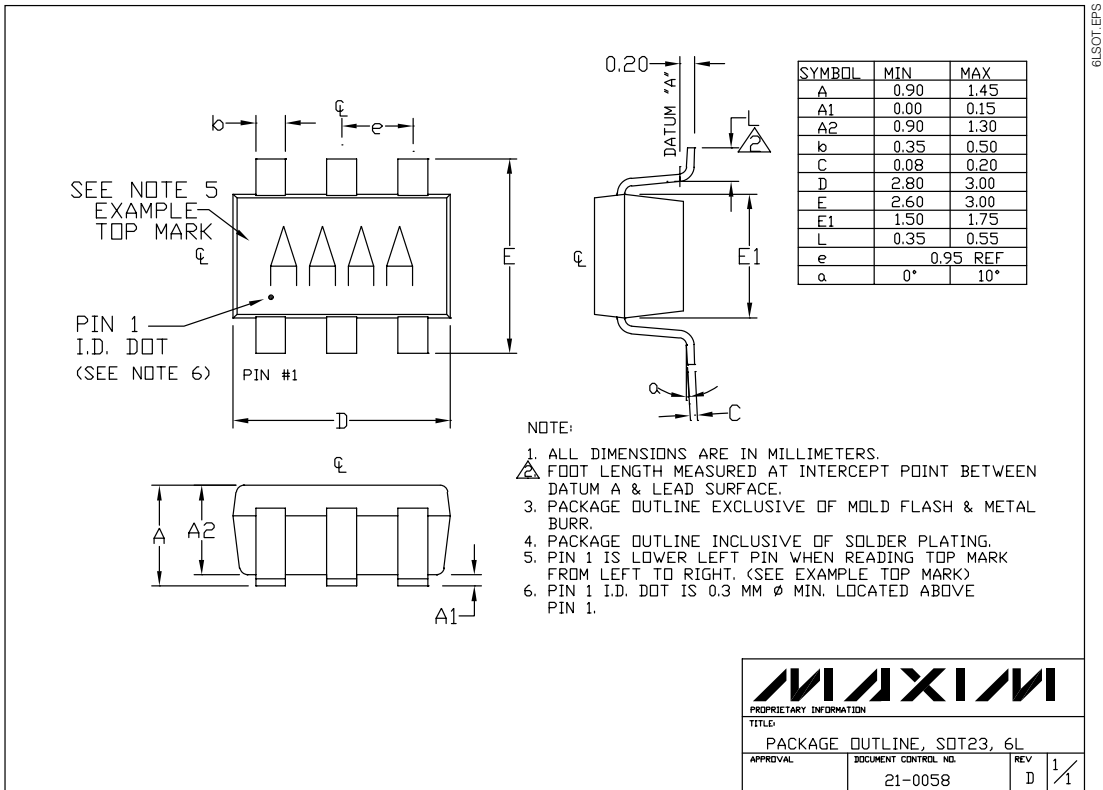


Figure 5. Channel On/Off-Capacitance

Package Information



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

8 Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 408-737-7600

© 2000 Maxim Integrated Products Printed USA MAXIM is a registered trademark of Maxim Integrated Products.